

<b>Notice of References Cited</b>	Application/Control No. 10/519,650		Applicant(s)/Patent Under Reexamination FRENCH ET AL.	
	Examiner DAVID GOODWIN		Art Unit 2818	Page 1 of 1

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2001/0051302	12-2001	DOVE et al.	430/5
*	B	US-5,882,827	03-1999	Nakao, Shuji	430/5
*	C	US-2002/0061452	05-2002	Nozawa et al.	430/5
	D	US-			
	E	US-			
	F	US-			
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	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Smith "Attenuated phase shift mask materials for 248 and 193 nm lithography" J.Vac. Sci. Technol. B Volume 14, issue 6, pp 3719-3723 (November 1996)
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.